Correction to: Channel Engineering Assisted Performance Enhancement of Metal Gate Sub-10nm Ballistic SiNWFET for Futuristic Device Applications

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Correction to: Silicon

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The original version of the article unfortunately contained an error.

A data was inadvertently added in the second author's affiliation Karamvir Singh. The correct author affiliation is shown below.

The original article has been corrected.

The online version of the original article can be found at <https://doi.org/10.1007/s12633-021-01459-9>

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